Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY DOCKET NO.		SERIAL NO. 10/828 32 New Application		
(MACAMAC)				251810US2				
				APPLICANT				
LIST OF	REFE	RENCES CITED BY AI	PPLICANT	Takahiro NAKAMOTO	· ·			
				FILING DATE Herewith  OY 212009		2815		
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
OUD/	AA	6,057,566	05/02/00	Kurt W. EISENBEISER, et al.	257	192		
	AB							
	X6-							
	AD							
	AE		$\overline{}$					
	AF			·	<u></u>	1		
	AG		1 .					
	AH				1 .			
	AI							
	AJ		<del></del>		$\forall$			
	AK		+		<del>  \</del>			
	AL				<del></del>		•	
	AM			<u> </u>		1	<u> </u>	
	AN		+					
	AN	L				L		
			FO	REIGN PATENT DOCUMENTS			•	
		DOCUMENT NUMBER	DATE	COUNTRY ( WY) WITH		TRANSLATION YES NO		
<u>~</u>	A0-		1		17 80 0	, , ,	, ,,,	
	AP							
	AQ	<u> </u>		·				
· · · · · · · · · · · · · · · · · · ·	AR				···			
	AS		+					
	AT		-		<del></del>			
	AU		+			<b>-</b>		
	AV		<del> </del>			ļ		
<del>-</del>	l v	<u> </u>				<u> </u>		
			<b>`</b>	Including Author, Title, Date, Pertine		•		
OHD.	w	R. E. WILLIAMS; et a ELECTRON DEVICE	il. "Graded Chai S, Vol. ED-25, I	nnel FET's: Improved Linearity and Noi No. 6, June 1978, pgs. 600-605	se Figure", I	EEE TRAN	SACTIONS ON	
OU US	2 <sub>AX</sub>	James A. ADAMS, et IEEE TRANSACTION	al. "Short-Char IS ON ELECTR	nel Effects and Drain-Induced Barrier I ON DEVICES, Vol. 40, No. 6, June 19	owering in 1 93, pgs. 104	Nanometer 7-1052	-Scale GaAs MESFET's",	
	AY							
	AZ	-						
					tional References sheet(s) attached			
Examiner	0	4 4 Chi	1		Date Co		9/18/05	
"Examiner: Ir conformance	itial if r	eference is considered t considered. Include of	, whether or not copy of this form	citation is in conformance with MPEP with next communication to applicant.	609; Draw li	ne through	citation if hot in	